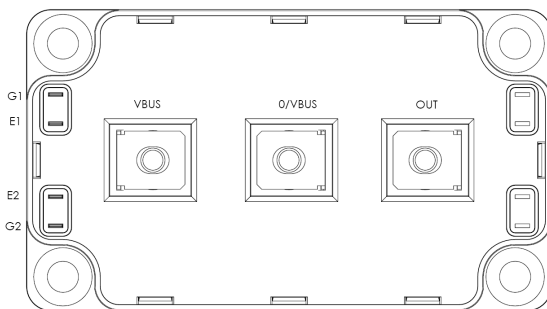
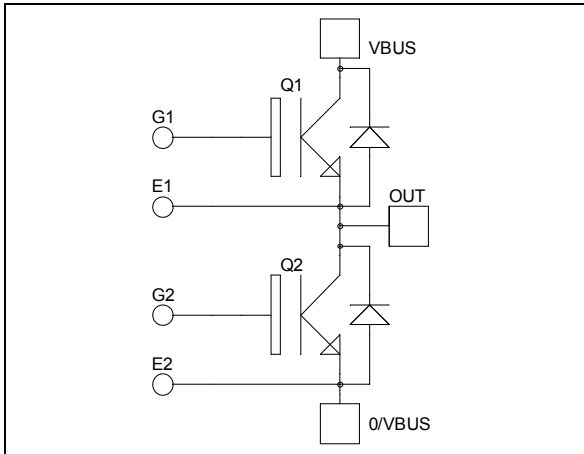


*Phase leg  
High speed Trench + Field Stop  
IGBT4 Power module*

**$V_{CES} = 1200V$   
 $I_C = 300A @ T_c = 80^\circ C$**



## Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

## Features

- **High speed Trench + Field Stop IGBT 4**
  - Low voltage drop
  - Low leakage current
  - Low switching losses
- Kelvin emitter for easy drive
- Very low stray inductance
- M5 power connectors

## Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS compliant

**All ratings @  $T_j = 25^\circ C$  unless otherwise specified**

## Absolute maximum ratings (Per IGBT)

| Symbol    | Parameter                    | Max ratings               | Unit |
|-----------|------------------------------|---------------------------|------|
| $V_{CES}$ | Collector - Emitter Voltage  | 1200                      | V    |
| $I_C$     | Continuous Collector Current | $T_C = 25^\circ C$<br>500 | A    |
|           |                              | $T_C = 80^\circ C$<br>300 |      |
| $I_{CM}$  | Pulsed Collector Current     | $T_C = 25^\circ C$<br>960 |      |
| $V_{GE}$  | Gate - Emitter Voltage       | $\pm 20$                  | V    |
| $P_D$     | Power Dissipation            | 1500                      | W    |



**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

## Electrical Characteristics (Per IGBT)

| Symbol        | Characteristic                       | Test Conditions                  | Min                                       | Typ         | Max          | Unit    |
|---------------|--------------------------------------|----------------------------------|-------------------------------------------|-------------|--------------|---------|
| $I_{CES}$     | Zero Gate Voltage Collector Current  | $V_{GE} = 0V, V_{CE} = 1200V$    |                                           |             | 200          | $\mu A$ |
| $V_{CE(sat)}$ | Collector Emitter Saturation Voltage | $V_{GE} = 15V$<br>$I_C = 300A$   | $T_j = 25^\circ C$<br>$T_j = 150^\circ C$ | 1.78<br>2.6 | 2.05<br>2.42 | V       |
| $V_{GE(th)}$  | Gate Threshold Voltage               | $V_{GE} = V_{CE}, I_C = 10.4 mA$ | 5.3                                       | 5.8         | 6.3          | V       |
| $I_{GES}$     | Gate – Emitter Leakage Current       | $V_{GE} = 20V, V_{CE} = 0V$      |                                           |             | 480          | nA      |

## Dynamic Characteristics (Per IGBT)

| Symbol       | Characteristic                      | Test Conditions                                                                                            | Min                 | Typ  | Max | Unit         |
|--------------|-------------------------------------|------------------------------------------------------------------------------------------------------------|---------------------|------|-----|--------------|
| $C_{ies}$    | Input Capacitance                   | $V_{GE} = 0V$                                                                                              |                     | 17.6 |     | nF           |
| $C_{oes}$    | Output Capacitance                  | $V_{CE} = 25V$                                                                                             |                     | 1    |     |              |
| $C_{res}$    | Reverse Transfer Capacitance        | $f = 1MHz$                                                                                                 |                     | 0.9  |     |              |
| $Q_G$        | Gate charge                         | $V_{GE} = 15V, I_C = 300A$<br>$V_{CE} = 960V$                                                              |                     | 1290 |     | nC           |
| $T_{d(on)}$  | Turn-on Delay Time                  | Inductive Switching (25°C)<br>$V_{GE} = \pm 15V$<br>$V_{Bus} = 600V$<br>$I_C = 300A$<br>$R_G = 1.6\Omega$  |                     | 30   |     | ns           |
| $T_r$        | Rise Time                           |                                                                                                            |                     | 57   |     |              |
| $T_{d(off)}$ | Turn-off Delay Time                 |                                                                                                            |                     | 290  |     |              |
| $T_f$        | Fall Time                           |                                                                                                            |                     | 16   |     |              |
| $T_{d(on)}$  | Turn-on Delay Time                  | Inductive Switching (150°C)<br>$V_{GE} = \pm 15V$<br>$V_{Bus} = 600V$<br>$I_C = 300A$<br>$R_G = 1.6\Omega$ |                     | 30   |     | ns           |
| $T_r$        | Rise Time                           |                                                                                                            |                     | 49   |     |              |
| $T_{d(off)}$ | Turn-off Delay Time                 |                                                                                                            |                     | 366  |     |              |
| $T_f$        | Fall Time                           |                                                                                                            |                     | 48   |     |              |
| $E_{on}$     | Turn on Energy                      | $V_{GE} = \pm 15V$<br>$V_{Bus} = 600V$<br>$I_C = 300A$<br>$R_G = 1.6\Omega$                                | $T_j = 150^\circ C$ | 26   |     | mJ           |
| $E_{off}$    | Turn off Energy                     |                                                                                                            | $T_j = 150^\circ C$ | 16   |     |              |
| $R_G$        | Integrated gate resistor            |                                                                                                            |                     | 2.5  |     | $\Omega$     |
| $I_{sc}$     | Short Circuit data                  | $V_{GE} \leq 15V; V_{Bus} = 600V$<br>$t_p \leq 10\mu s; T_j = 150^\circ C$                                 |                     | 1000 |     | A            |
| $R_{thJC}$   | Junction to Case Thermal Resistance |                                                                                                            |                     |      | 0.1 | $^\circ C/W$ |

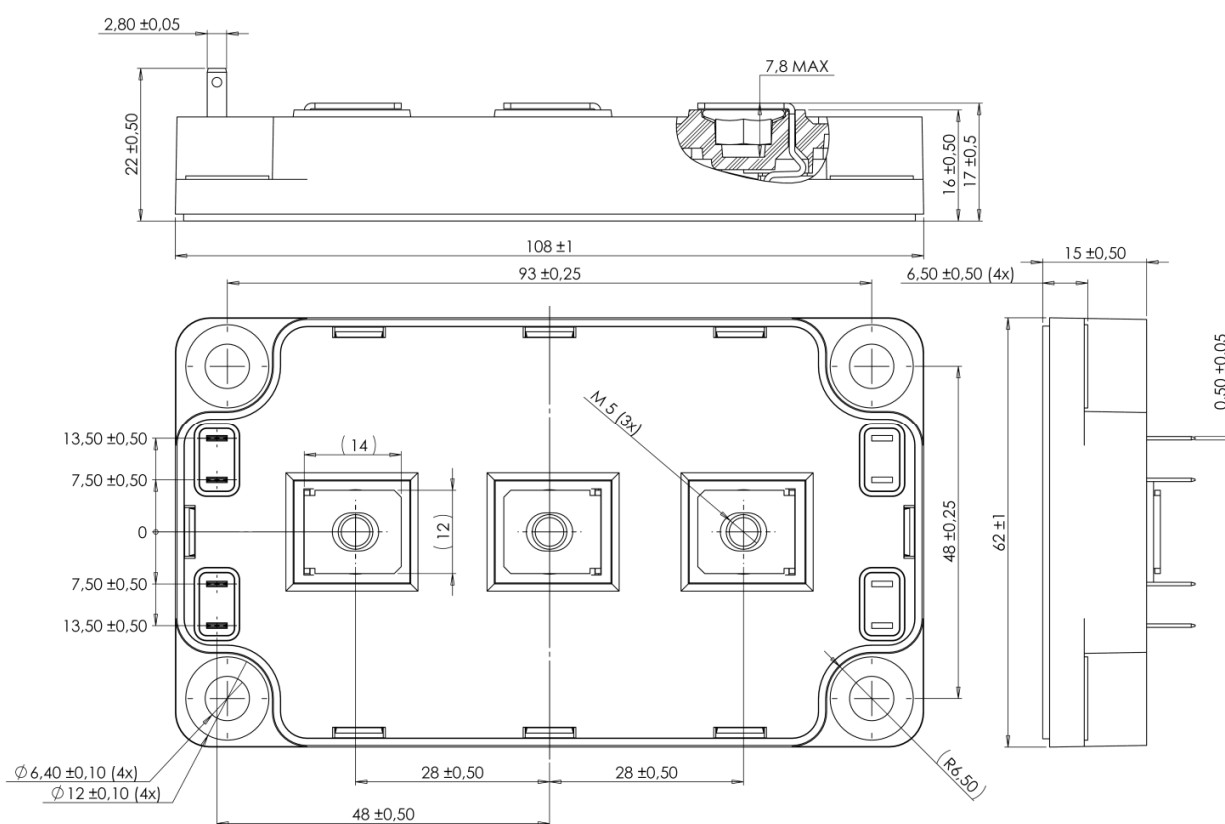
## Diode ratings and characteristics (per diode)

| Symbol     | Characteristic                      | Test Conditions                                      | Min                                       | Typ          | Max  | Unit         |
|------------|-------------------------------------|------------------------------------------------------|-------------------------------------------|--------------|------|--------------|
| $V_{RRM}$  | Peak Repetitive Reverse Voltage     |                                                      |                                           |              | 1200 | V            |
| $I_{RM}$   | Reverse Leakage Current             | $V_R = 1200V$                                        |                                           |              | 400  | $\mu A$      |
| $I_F$      | DC Forward Current                  | $T_c = 60^\circ C$                                   |                                           | 240          |      | A            |
| $V_F$      | Diode Forward Voltage               | $I_F = 240A$                                         |                                           | 2.5          | 3.5  | V            |
|            |                                     | $I_F = 480A$                                         |                                           | 3            |      |              |
|            |                                     | $I_F = 240A, T_j = 125^\circ C$                      |                                           | 1.8          |      |              |
| $t_{rr}$   | Reverse Recovery Time               | $I_F = 240A$<br>$V_R = 800V$<br>$di/dt = 800A/\mu s$ | $T_j = 25^\circ C$<br>$T_j = 125^\circ C$ | 265<br>350   |      | ns           |
| $Q_{rr}$   | Reverse Recovery Charge             |                                                      | $T_j = 25^\circ C$<br>$T_j = 125^\circ C$ | 2.24<br>11.6 |      |              |
| $R_{thJC}$ | Junction to Case Thermal Resistance |                                                      |                                           |              | 0.17 | $^\circ C/W$ |

## Thermal and package characteristics

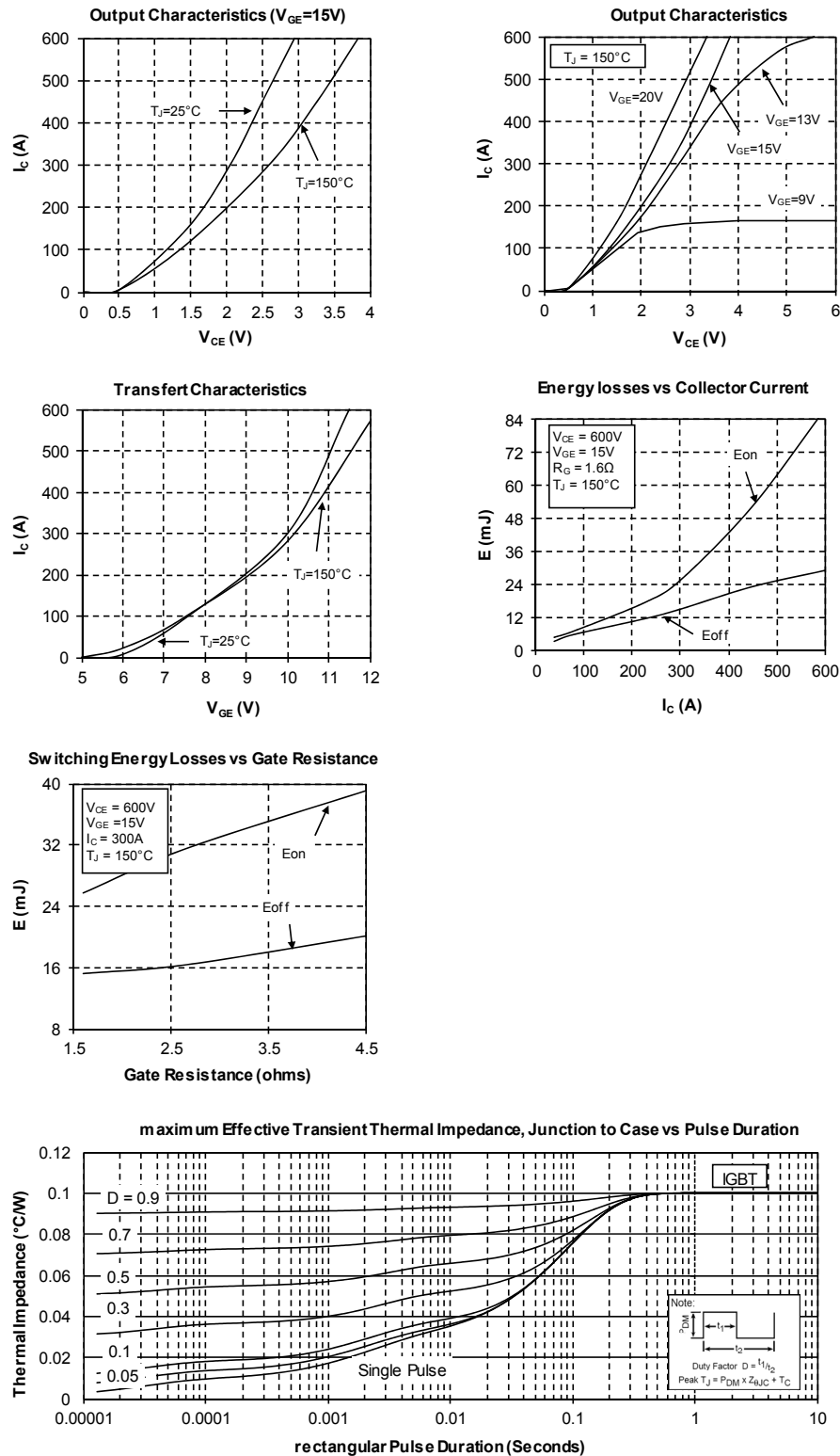
| Symbol            | Characteristic                                                |               |    | Min  | Max                    | Unit |
|-------------------|---------------------------------------------------------------|---------------|----|------|------------------------|------|
| V <sub>ISOL</sub> | RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz |               |    | 4000 |                        | V    |
| T <sub>J</sub>    | Operating junction temperature range                          |               |    | -40  | 175                    | °C   |
| T <sub>JOP</sub>  | Recommended junction temperature under switching conditions   |               |    | -40  | T <sub>J</sub> max -25 |      |
| T <sub>STG</sub>  | Storage Temperature Range                                     |               |    | -40  | 125                    |      |
| T <sub>C</sub>    | Operating Case Temperature                                    |               |    | -40  | 125                    |      |
| Torque            | Mounting torque                                               | To heatsink   | M6 | 3    | 5                      | N.m  |
|                   |                                                               | For terminals | M5 | 2    | 3.5                    |      |
| Wt                | Package Weight                                                |               |    |      | 300                    | g    |

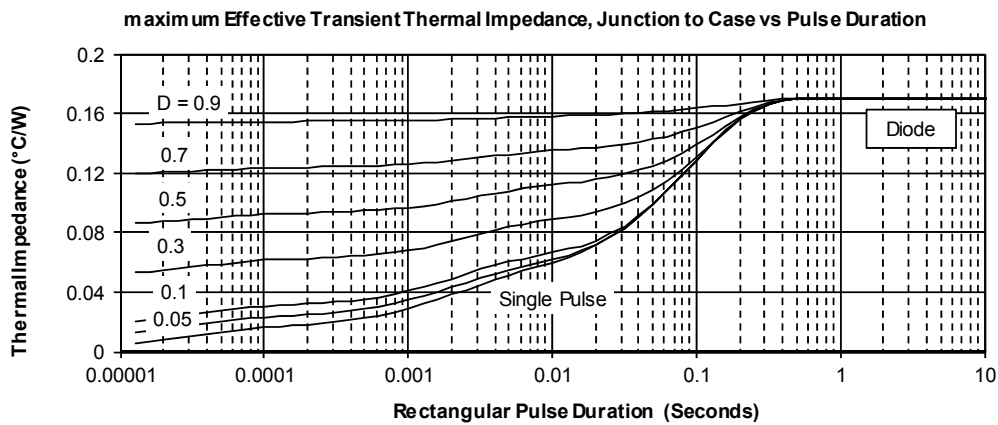
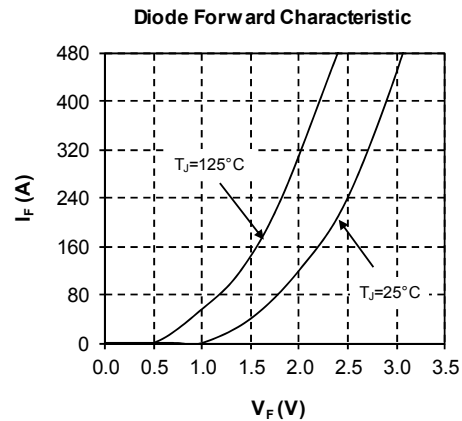
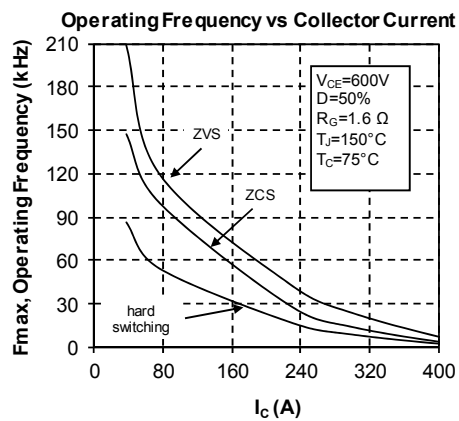
### Package outline (dimensions in mm)



See application note APT0601 - Mounting Instructions for SP6 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve





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